

INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT PTO-1449Docket No.  
**52433/858**Application No.  
**10/589,680**

Applicant(s)

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Examiner

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## U. S. PATENT DOCUMENTS

EXAMINER INITIAL	PATENT/PUBLICATION NUMBER	PATENT/PUBLICATION DATE mm/dd/yyyy	NAME	CLASS	SUBCLASS	FILING DATE*
/JL/	<b>5,856,231</b>	<b>01/05/1999</b>	<b>Niemann et al.</b>			

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE mm/dd/yyyy	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						Yes	No
/JL/	<b>9-500861</b>	<b>01/28/97</b>	<b>Japan</b>			<b>corresponds to US Patent No. 5,856,231</b>	

## OTHER DOCUMENTS

EXAMINER INITIAL	AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.
/JL/	Yu. M. Tairov et al. "General Principles of Growing Large-Size Single Crystals of Various Silicon Carbide Polotypes" Journal of Crystal Growth 52 (1981) 146-150
/JL/	S.A. Reshanov et al., "Features of Semi-Insulating SiC Single-Crystal Growth by Physical Vapor Transport" Materials Science Forum Vols. 353-356 (2001) pp 53-56
/JL/	M. Bickermann et al., "On the Preparation of Vanadium-Doped Semi-Insulating SiC Bulk Crystals" Materials Science Forum Vols. 389-393 (2002) pp. 139-142
/JL/	M.E. Zvanut et al. "The level position of a deep intrinsic defect in 4H-SiC studied by photoinduced electron paramagnetic resonance." Applied Physics Letters. Volume 80, Number 3. 21 January 2002 pp 410-412.
/JL/	B. Magnusson et al. "Properties of the UD-1 Deep-Level Center in 4H-SiC" Materials Science Forum Vols. 389-393 (2002) pp 505-508
/JL/	K. Rammohan et al., "Gallium Nitride: A Material Opportunity" Rutberg & Co.. 2001, pp 1-53

EXAMINER	DATE CONSIDERED
/JL/ /Jonathan Langman/	11/25/2009
EXAMINER: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	